

In the Claims:

Please amend the claims as indicated below. This listing of claims replaces all prior versions.

1. *(Currently Amended)* A method of manufacturing a semiconductor device, the method comprising:

applying an auxiliary layer comprising non-doped silicon and germanium to
~~wherein a surface of a silicon body is provided with an auxiliary layer of a material on~~
~~which~~ wherein, during an oxidation treatment, a thicker layer of silicon oxide is formed
on the auxiliary layer than is formed on the silicon surface of the silicon body;~~after~~
~~which;~~

at the location of field isolation regions to be formed, forming windows ~~are~~
~~formed~~ in the auxiliary layer and grooves ~~are formed~~ in the surface of the silicon body;

~~whereafter carrying out an oxidation treatment is carried out wherein to provide~~
the walls of the grooves and of the windows ~~are provided~~ respectively of the silicon body
and the auxiliary layer with a layer of silicon oxide, the silicon oxide on the auxiliary
layer being thicker than the silicon oxide on the silicon body;

but wherein it is precluded that the auxiliary layer adjacent to the windows is
oxidized across the entire thickness;

after which, successively, a layer of isolating material is deposited in a thickness
such that the grooves and the windows are filled completely; and

carrying out a planarization treatment ~~is carried out~~ until the non-oxidized part of
the auxiliary layer is exposed, after which this part of the auxiliary layer is removed;
~~characterized in that a layer comprising silicon and germanium is applied as an auxiliary~~
~~layer to the surface of the silicon body.~~

2. *(Original)* A method as claimed in claim 1, characterized in that on the surface of the
silicon body a layer of $\text{Si}_x\text{Ge}_{1-x-y}\text{C}_y$, where $0.70 < x < 0.95$ and $y < 0.05$, is provided as the
auxiliary layer.

3. (*Previously Presented*) A method as claimed in claim 1, characterized in that the auxiliary layer is applied in a thickness such that this layer is not converted across the entire thickness into an oxide during the oxidation treatment.
4. (*Previously Presented*) A method as claimed in claim 1, characterized in that a layer of silicon nitride is applied to the auxiliary layer, the windows being formed in the layer of silicon nitride as well as in the auxiliary layer.
5. (*Previously Presented*) A method as claimed in claim 1, characterized in that prior to applying the auxiliary layer to the surface of the silicon body, this surface is provided with a layer of silicon oxide, and the windows are also formed in the layer of silicon oxide.
6. (*Previously Presented*) A method as claimed in claim 2, characterized in that the auxiliary layer is applied in a thickness such that this layer is not converted across the entire thickness into an oxide during the oxidation treatment.
7. (*Previously Presented*) A method as claimed in claim 2, characterized in that a layer of silicon nitride is applied to the auxiliary layer, the windows being formed in the layer of silicon nitride as well as in the auxiliary layer.
8. (*Previously Presented*) A method as claimed in claim 2, characterized in that prior to applying the auxiliary layer to the surface of the silicon body, this surface is provided with a layer of silicon oxide, and the windows are also formed in the layer of silicon oxide.
9. (*Previously Presented*) A method as claimed in claim 3, characterized in that prior to applying the auxiliary layer to the surface of the silicon body, this surface is provided with a layer of silicon oxide, and the windows are also formed in the layer of silicon oxide.

10. (*Previously Presented*) A method as claimed in claim 4, characterized in that prior to applying the auxiliary layer to the surface of the silicon body, this surface is provided with a layer of silicon oxide, and the windows are also formed in the layer of silicon oxide.

11. (*New*) A method of manufacturing a semiconductor device, the method comprising:

applying an non-doped auxiliary layer comprising silicon and germanium to a substrate including silicon, the non-doped auxiliary layer having oxidation characteristics that facilitate thicker oxide growth, relative to oxide growth on the substrate;

forming an opening having walls extending through the auxiliary layer and into the silicon body;

oxidizing the auxiliary layer and the silicon body at the walls of the opening to form a layer of silicon oxide on the auxiliary layer that is thicker than the silicon oxide layer on the silicon body, wherein the auxiliary layer adjacent to the wall is not oxidized across its entire thickness;

depositing a layer of isolating material on the layer of silicon dioxide to fill the opening;

planarizing the semiconductor device to expose a non-oxidized part of the auxiliary layer; and

after planarization, removing the non-oxidized part of the auxiliary layer.